

N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
200	0.240 at $V_{GS} = 10$ V	2.2
	0.260 at $V_{GS} = 6.0$ V	2.1

FEATURES

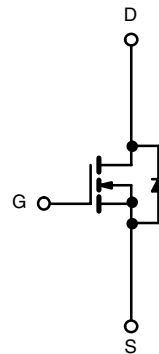
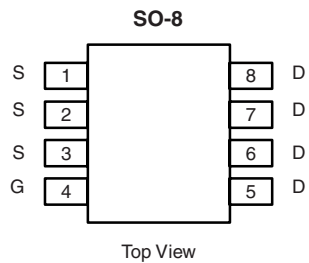
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- PWM Optimized for Low Q_g and Low R_g
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Primary Side Switch



Ordering Information: Si4464DY-T1-E3 (Lead (Pb)-free)
Si4464DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	200		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	2.2	1.7	A
	T _A = 70 °C		1.7	1.3	
Pulsed Drain Current		I _{DM}	8		
Single Avalanche Current	L = 0.1 mH	I _{AS}	3		
Single Avalanche Energy		E _{AS}	0.45		mJ
Continuous Source Current (Diode Conduction) ^a		I _S	2.1	1.2	A
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.5	1.5	W
	T _A = 70 °C		1.6	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	37	50	$^\circ\text{C/W}$
		68	85	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0		4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	8			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 2.2\text{ A}$		0.195	0.240	Ω
		$V_{GS} = 6.0\text{ V}$, $I_D = 2.1\text{ A}$		0.210	0.260	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 2.2\text{ A}$		8.0		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.1\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 100\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 2.2\text{ A}$		12	18	nC
Gate-Source Charge	Q_{gs}			2.5		
Gate-Drain Charge	Q_{gd}			3.8		
Gate Resistance	R_g			2.5		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$, $R_L = 100\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		10	15	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			15	25	
Fall Time	t_f			15	25	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.1\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$		60	90	

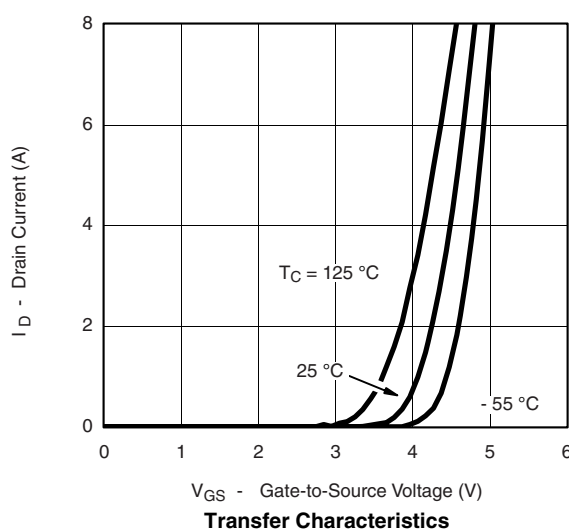
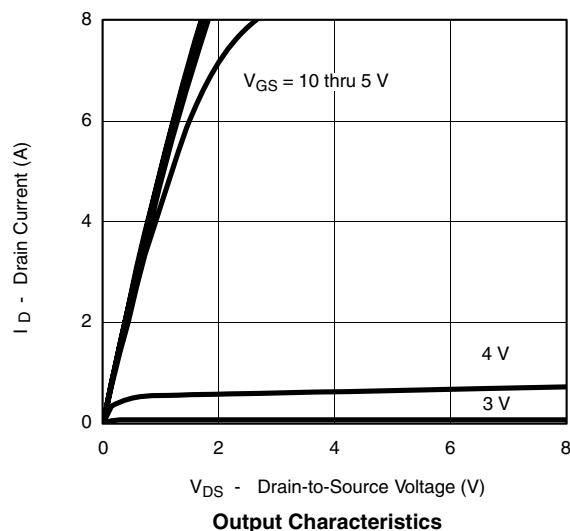
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

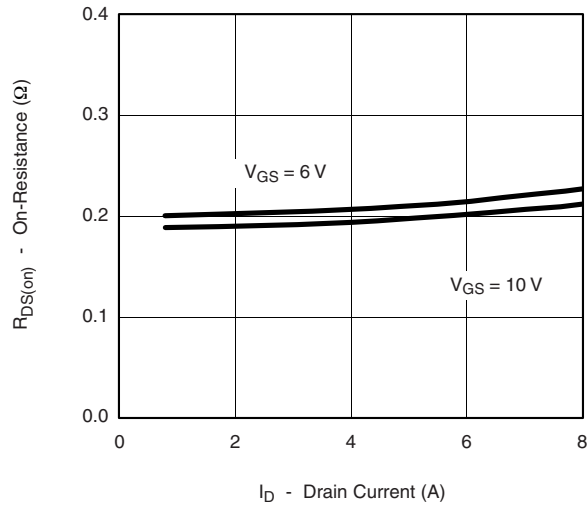
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

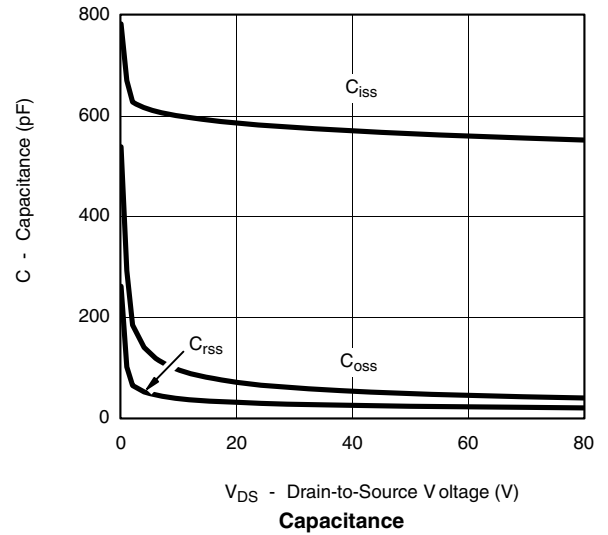
TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted



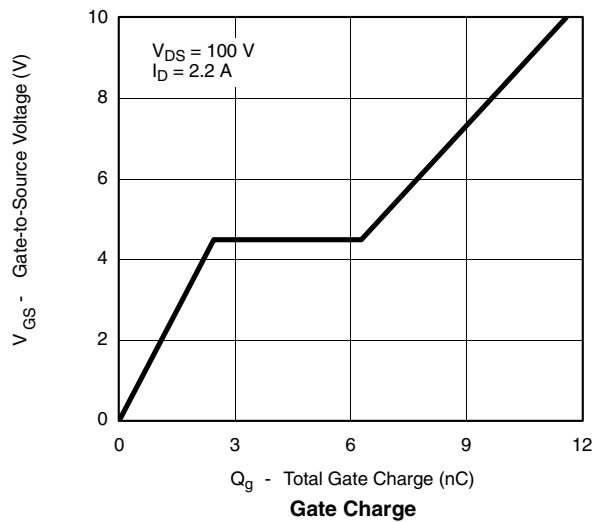
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



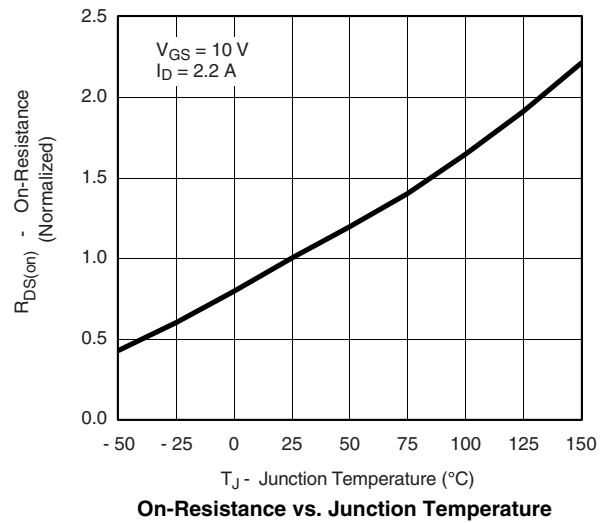
On-Resistance vs. Drain Current



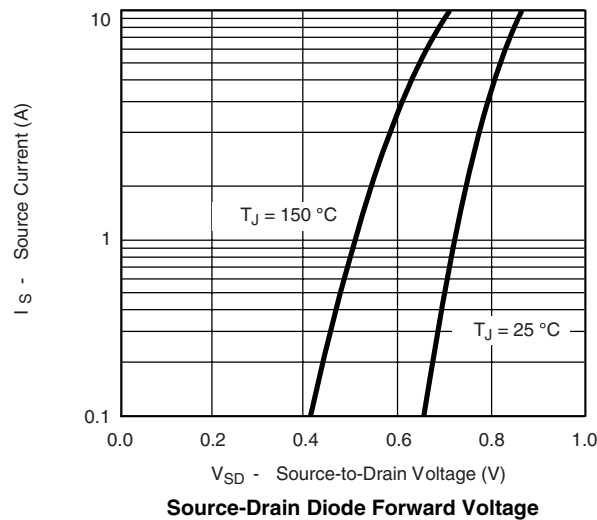
Capacitance



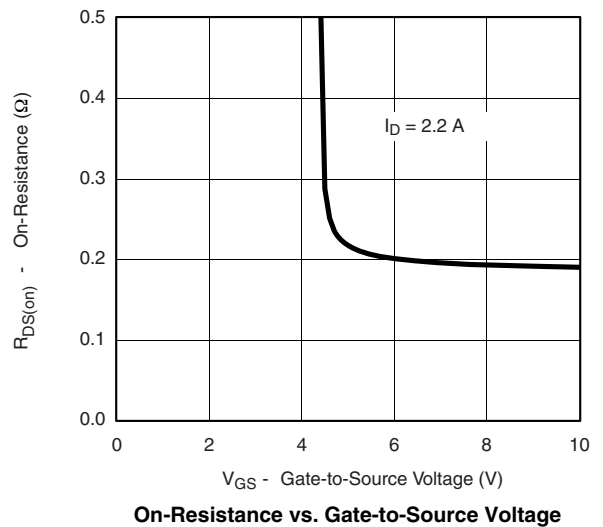
Gate Charge



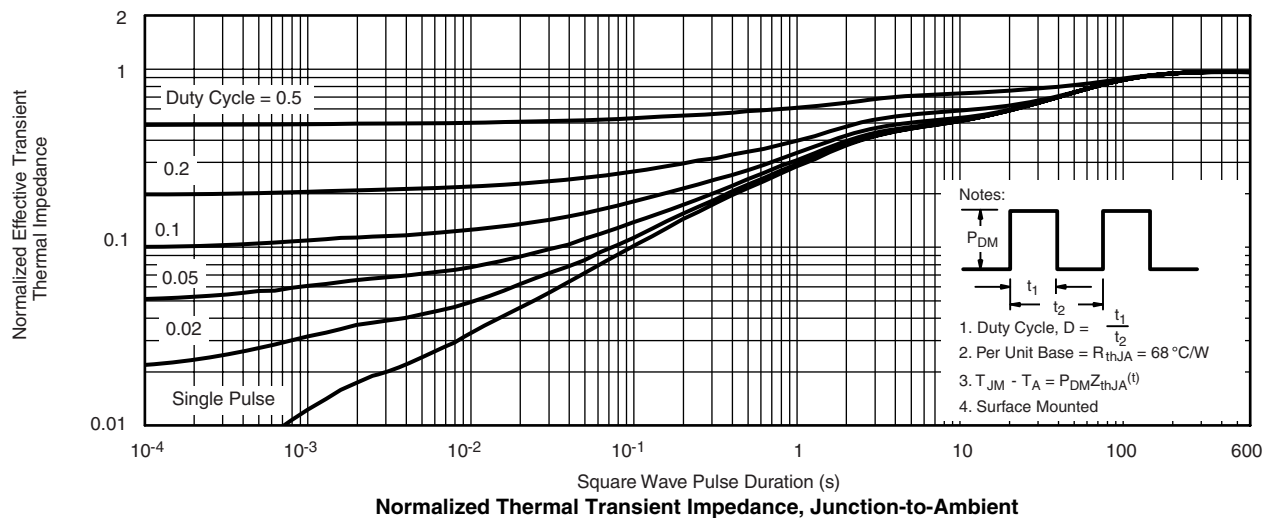
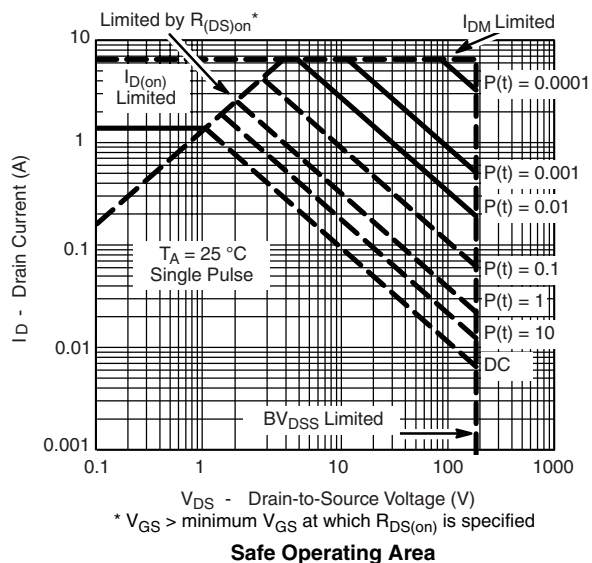
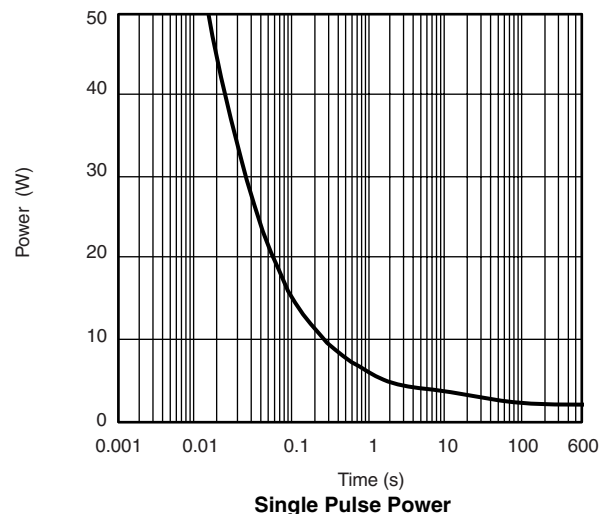
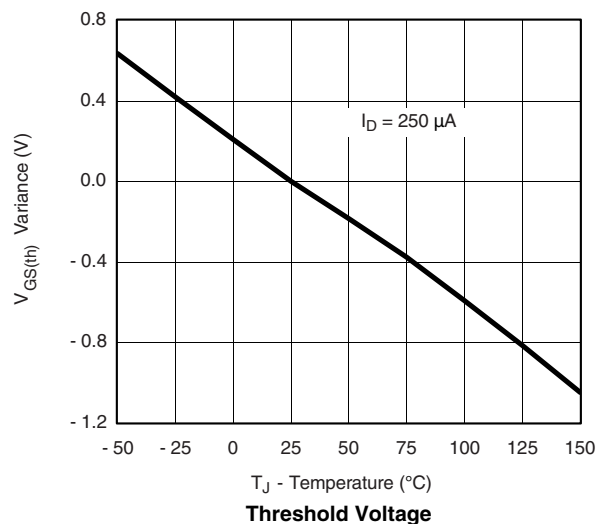
On-Resistance vs. Junction Temperature



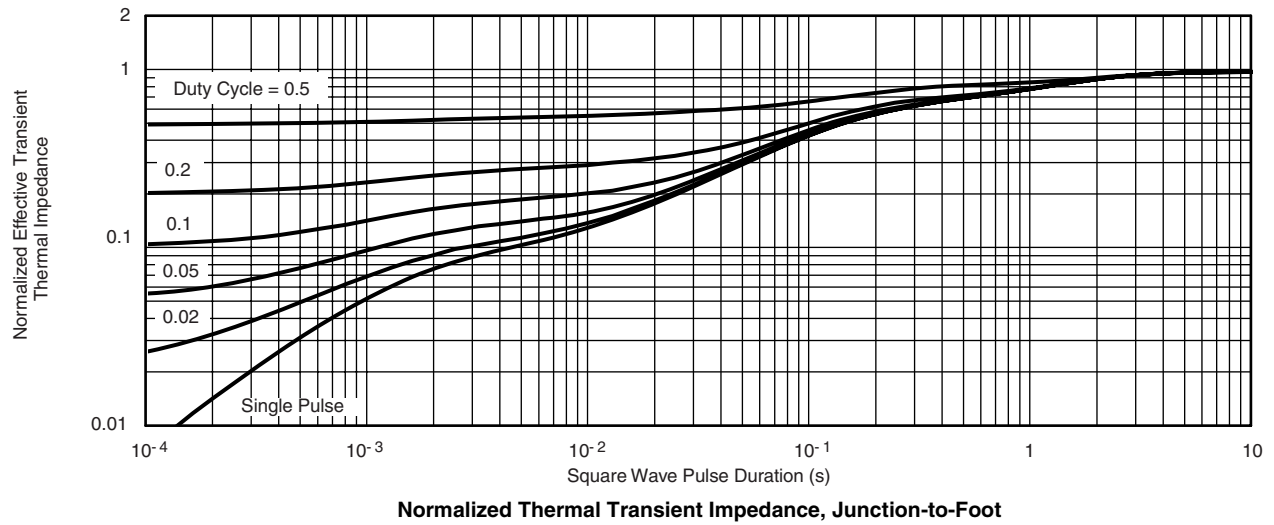
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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